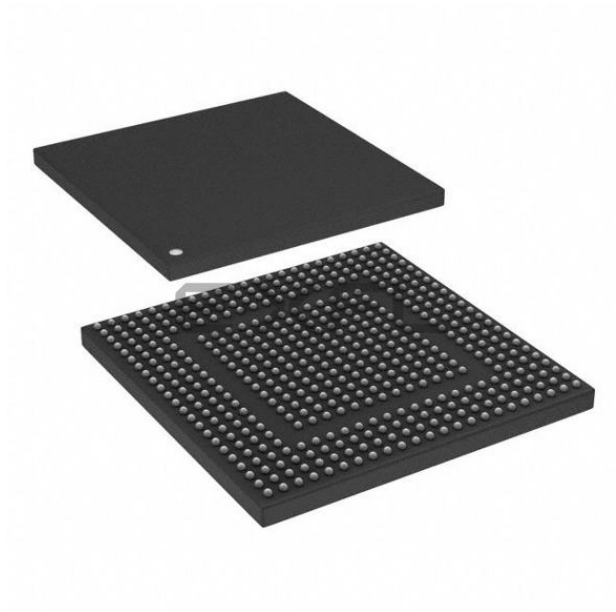

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z7d
Core Size	32-Bit Dual-Core
Speed	180MHz
Connectivity	CANbus, EBI/EMI, Ethernet, FlexRay, I²C, LINbus, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	-
Program Memory Size	1.5MB (1.5M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	384K x 8
Voltage - Supply (Vcc/Vdd)	1.14V ~ 5.5V
Data Converters	A/D 34x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	473-LFBGA
Supplier Device Package	473-MAPBGA (19x19)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5674kf0vms2

Table 1. MPC5675K family device comparison (continued)

Features		MPC5673K	MPC5674K	MPC5675K
Packages	MAPBGA	257 pins 473 pins		
Temperature	Ambient	See the T_A recommended operating condition in the device data sheet		

1 Sphere of Replication.

2 Does not include Test or Shadow Flash memory space.

3 DSPI_0 and DSPI_1.

4 DSPI_0 has 8 chip selects; DSPI_1 and DSPI_2 have 4 chip selects each.

5 Available only on 473-pin package.

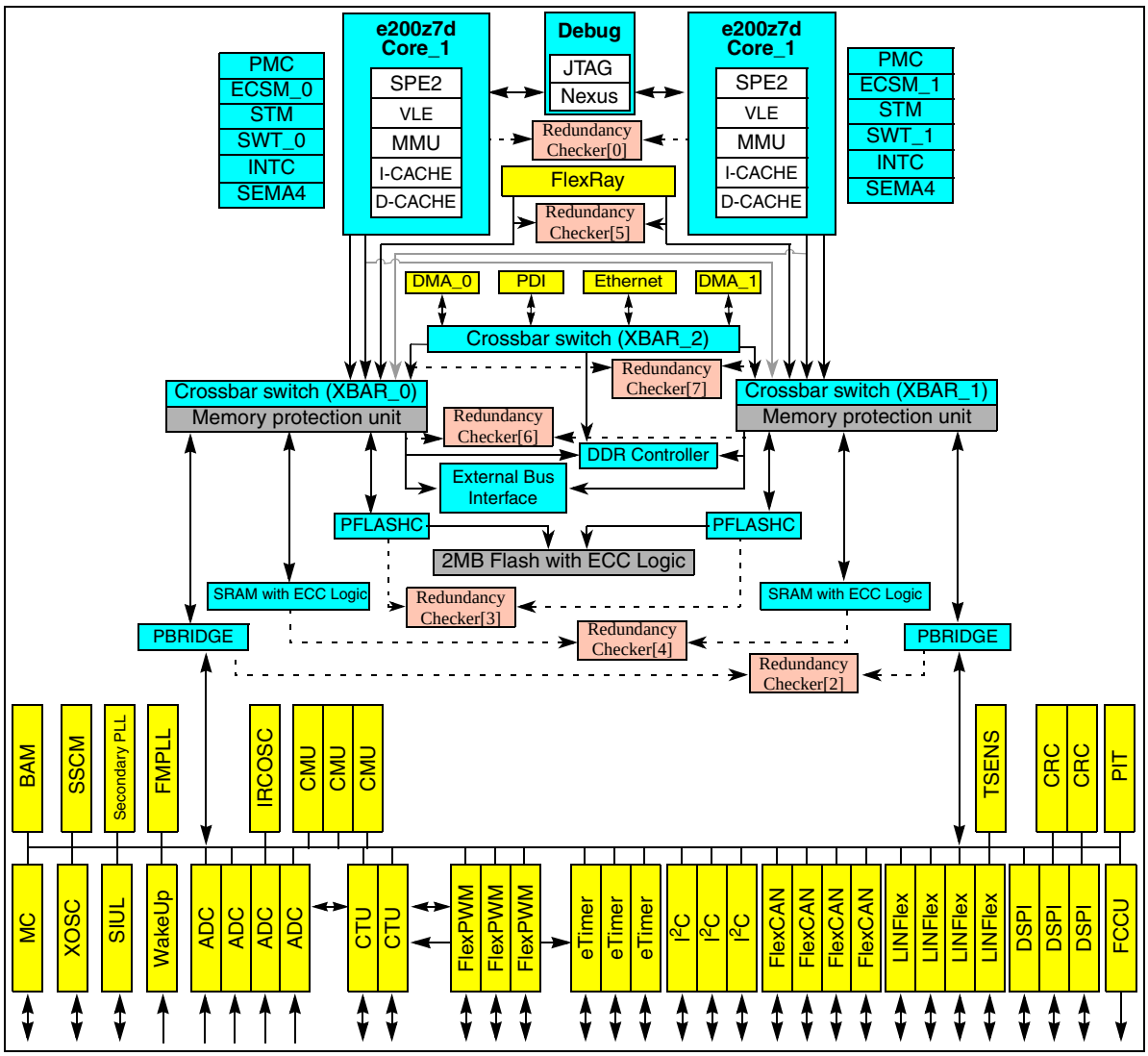
6 I2C_0 and I2C_1.

7 LinFlex_0, LinFlex_1, and LinFlex_2.

8 DDR available only on 473 package. Other modules available as follows:
EBI or DDR on 473 package
EBI + PDI on 473 package
DDR + PDI on 473 package
PDI only on 257 package

1.4 Block diagram

Figure 1 shows a top-level block diagram of the MPC5675K device.



ADC – Analog-to-digital converter
BAM – Boot assist module
CMU – Clock monitoring unit
CRC – Cyclic redundancy check unit
CTU – Cross triggering unit
DSPI – Deserial serial peripheral interface
EBI – External bus interface
ECC – Error correction code
ECSM – Error correction status module
eDMA – Enhanced direct memory access controller
FCCU – Fault collection and control unit
FEC – Fast Ethernet controller
FlexCAN – Controller area network controller
FlexPWM – Pulse width modulator module
FMPLL – Frequency-modulated phase-locked loop
I2C – Inter-integrated circuit controller
INTC – Interrupt controller
IRCOSC – Internal RC oscillator
JTAG – Joint Test Action Group interface
MC – Mode entry, clock, reset, and power modules
mDDR – Mobile double data rate dynamic RAM
PBRIDGE – Peripheral bridge
PDI – Parallel data interface
PIT – Periodic interrupt timer
PMC – Power management controller
RC – Redundancy checker
RTC – Real time clock
SEMA4 – Semaphore unit
SIUL – System integration unit Lite
SSCM – System status and configuration module
STM – System timer module
SWT – Software watchdog timer
TSENS – Temperature sensor
XOSC – Crystal oscillator

Figure 1. MPC5675K block diagram

Table 9. 257 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional inputs	Analog inputs	Weak pull during reset	Pad type	Power domain
C7	GPIO	etimer0 ETC[1]	A0: siul_GPIO[1] A1: etimer0_ETC[1] A2: _ A3: _	I: _ I: _ I: siul_EIRQ[1]	—	disabled	GP Slow/ Medium	VDD_HV_IO
C8	GPIO	etimer0 ETC[2]	A0: siul_GPIO[2] A1: etimer0_ETC[2] A2: _ A3: _	I: _ I: _ I: siul_EIRQ[2]	—	disabled	GP Slow/ Medium	VDD_HV_IO
C9	GPIO	etimer0 ETC[3]	A0: siul_GPIO[3] A1: etimer0_ETC[3] A2: _ A3: _	I: _ I: mc_rgm_ABS[2] I: siul_EIRQ[3]	—	pulldown	GP Slow/ Medium	VDD_HV_IO
C11	GPIO	fec CRS	A0: siul_GPIO[208] A1: flexray_DBG1 A2: etimer2_ETC[3] A3: dspi0_CS5	I: fec_CRS I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
C12	GPIO	fec TXD[0]	A0: siul_GPIO[201] A1: fec_TXD[0] A2: etimer2_ETC[1] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
C13	GPIO	fec COL	A0: siul_GPIO[206] A1: fec_COL A2: _ A3: lin1_TXD	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
C14	GPIO	can0 RXD	A0: siul_GPIO[17] A1: _ A2: _ A3: sscm_DEBUG[1]	I: can0_RXD I: can1_RXD I: siul_EIRQ[16]	—	disabled	GP Slow/ Medium	VDD_HV_IO
C16	GPIO	pdi DATA[5]	A0: siul_GPIO[136] A1: flexpwm2_A[0] A2: _ A3: etimer1_ETC[0]	I: pdi_DATA[5] I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI
C17	GPIO	pdi CLOCK	A0: siul_GPIO[128] A1: flexpwm2_B[1] A2: _ A3: etimer1_ETC[3]	I: pdi_CLOCK I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI

Table 9. 257 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional inputs	Analog inputs	Weak pull during reset	Pad type	Power domain
D1	GPIO	nexus MDO[2][1]	A0: siul_GPIO[85] A1: _ A2: npc_wrapper_MDO[2] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
D2	GPIO	nexus MDO[3][1]	A0: siul_GPIO[84] A1: _ A2: npc_wrapper_MDO[3] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
D3	GPIO	can1 RXD	A0: siul_GPIO[15] A1: _ A2: _ A3: _	I: can1_RXD I: can0_RXD I: siul_EIRQ[14]	—	disabled	GP Slow/ Medium	VDD_HV_IO
D4	GPIO	dspi0 SOUT	A0: siul_GPIO[38] A1: dspi0_SOUT A2: _ A3: sscm_DEBUG[6]	I: _ I: _ I: siul_EIRQ[24]	—	disabled	GP Slow/ Medium	VDD_HV_IO
D6	GPIO	etimer0 ETC[5]	A0: siul_GPIO[44] A1: etimer0_ETC[5] A2: _ A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
D7	GPIO	etimer0 ETC[4]	A0: siul_GPIO[43] A1: etimer0_ETC[4] A2: _ A3: _	I: _ I: mc_rgm_ABS[0] I: _	—	pulldown	GP Slow/ Medium	VDD_HV_IO
D10	GPIO	fec TXD[2]	A0: siul_GPIO[203] A1: fec_TXD[2] A2: _ A3: _	I: flexpwm1_FAULT[1] I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
D11	GPIO	fec TXD[1]	A0: siul_GPIO[202] A1: fec_TXD[1] A2: _ A3: dspi2_SCK	I: flexpwm1_FAULT[0] I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
D12	GPIO	fec RX_DV	A0: siul_GPIO[210] A1: flexray_DBG3 A2: etimer2_ETC[0] A3: dspi0_CS7	I: fec_RX_DV I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO

Table 10. 473 MAPBGA pin multiplexing

Ball number	Ball type	Ball name	Alternate I/O	Additional Inputs	Analog Inputs	Weak pull during reset	Pad type	Power domain
A4	GPIO	nexus MDO[5][1]	A0: siul_GPIO[114] A1: _ A2: npc_wrapper_MDO[5] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
A5	GPIO	nexus MDO[7][1]	A0: siul_GPIO[112] A1: _ A2: npc_wrapper_MDO[7] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
A6	GPIO	nexus MDO[9][1]	A0: siul_GPIO[110] A1: _ A2: npc_wrapper_MDO[9] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
A7	GPIO	flexray CB_TX	A0: siul_GPIO[51] A1: flexray_CB_TX A2: _ A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Symmetric	VDD_HV_IO
A8	GPIO	flexray CA_TR_EN	A0: siul_GPIO[47] A1: flexray_CA_TR_EN A2: _ A3: _	I: ctu0_EXT_IN I: flexpwm0_EXT_SYNC I: _	—	disabled	GP Slow/ Symmetric	VDD_HV_IO
A9	GPIO	fec RX_DV	A0: siul_GPIO[210] A1: flexray_DBG3 A2: etimer2_ETC[0] A3: dspi0_CS7	I: fec_RX_DV I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
A10	GPIO	fec MDIO	A0: siul_GPIO[198] A1: fec_MDIO A2: _ A3: dspi2_CS0	I: _ I: _ I: siul_EIRQ[28]	—	disabled	GP Slow/ Medium	VDD_HV_IO
A11	GPIO	fec TX_CLK	A0: siul_GPIO[207] A1: flexray_DBG0 A2: etimer2_ETC[4] A3: dspi0_CS4	I: fec_TX_CLK I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
A12	GPIO	fec TX_EN	A0: siul_GPIO[200] A1: fec_TX_EN A2: _ A3: lin0_TXD	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO

Table 10. 473 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional Inputs	Analog Inputs	Weak pull during reset	Pad type	Power domain
A13	GPIO	fec TXD[3]	A0: siul_GPIO[204] A1: fec_TXD[3] A2: _ A3: dspi2_CS2	I: flexpwm1_FAULT[2] I: _ I: siul_EIRQ[29]	—	disabled	GP Slow/ Medium	VDD_HV_IO
A15	GPIO	pdi DATA[3]	A0: siul_GPIO[134] A1: flexpwm2_X[1] A2: _ A3: _	I: pdi_DATA[3] I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI
A16	GPIO	pdi DATA[1]	A0: siul_GPIO[132] A1: flexpwm2_B[3] A2: _ A3: _	I: pdi_DATA[1] I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI
A17	GPIO	pdi CLOCK	A0: siul_GPIO[128] A1: flexpwm2_B[1] A2: _ A3: etimer1_ETC[3]	I: pdi_CLOCK I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI
A18	GPIO	pdi DATA[7]	A0: siul_GPIO[138] A1: flexpwm2_B[2] A2: _ A3: etimer1_ETC[5]	I: pdi_DATA[7] I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI
A19	GPIO	pdi DATA[10]	A0: siul_GPIO[141] A1: flexpwm2_X[3] A2: _ A3: _	I: pdi_DATA[10] I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI
A20	GPIO	pdi DATA[13]	A0: siul_GPIO[144] A1: pdi_SENS_SEL[2] A2: ctu1_EXT_TGR A3: _	I: pdi_DATA[13] I: _ I: _	—	disabled	PDI Medium	VDD_HV_PDI
A21	GPIO	pdi DATA[15]	A0: siul_GPIO[146] A1: pdi_SENS_SEL[0] A2: i2c2_data A3: _	I: pdi_DATA[15] I: ctu1_EXT_IN I: _	—	disabled	PDI Medium	VDD_HV_PDI
B3	GPIO	mc_cgl clk_out	A0: siul_GPIO[22] A1: mc_cgl_clk_out A2: etimer2_ETC[5] A3: _	I: _ I: _ I: siul_EIRQ[18]	—	disabled	GP Slow/ Fast	VDD_HV_IO

Table 10. 473 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional Inputs	Analog Inputs	Weak pull during reset	Pad type	Power domain
B4	GPIO	can1 TXD	A0: siul_GPIO[14] A1: can1_TXD A2: _ A3: _	I: _ I: _ I: siul_EIRQ[13]	—	disabled	GP Slow/ Medium	VDD_HV_IO
B5	GPIO	nexus MDO[14][1]	A0: siul_GPIO[219] A1: _ A2: npc_wrapper_MDO[14] A3: can3_TXD	I: _ I: _ I: _	—	disabled	GP Slow/ Fast	VDD_HV_IO
B6	GPIO	dspi2 CS1	A0: siul_GPIO[9] A1: dspi2_CS1 A2: _ A3: _	I: flexpwm0_FAULT[0] I: lin3_RXD I: can2_RXD	—	disabled	GP Slow/ Medium	VDD_HV_IO
B7	GPIO	flexray CB_TR_EN	A0: siul_GPIO[52] A1: flexray_CB_TR_EN A2: _ A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Symmetric	VDD_HV_IO
B8	GPIO	flexray CA_TX	A0: siul_GPIO[48] A1: flexray_CA_TX A2: _ A3: _	I: ctu1_EXT_IN I: _ I: _	—	disabled	GP Slow/ Symmetric	VDD_HV_IO
B9	GPIO	fec RXD[3]	A0: siul_GPIO[214] A1: i2c1_data A2: _ A3: _	I: fec_RXD[3] I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
B10	GPIO	fec RX_ER	A0: siul_GPIO[215] A1: _ A2: _ A3: dspi0_CS1	I: fec_RX_ER I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
B11	GPIO	fec TXD[0]	A0: siul_GPIO[201] A1: fec_TXD[0] A2: etimer2_ETC[1] A3: _	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
B12	GPIO	fec RXD[0]	A0: siul_GPIO[211] A1: i2c1_clock A2: _ A3: _	I: fec_RXD[0] I: _ I: siul_EIRQ[27]	—	disabled	GP Slow/ Medium	VDD_HV_IO

Table 10. 473 MAPBGA pin multiplexing (continued)

Ball number	Ball type	Ball name	Alternate I/O	Additional Inputs	Analog Inputs	Weak pull during reset	Pad type	Power domain
Y22	GPIO	dramc ADD[11]	A0: siul_GPIO[169] A1: dramc_ADD[11] A2: ebi_AD3 A3: ebi_ADD19	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
Y23	GPIO	dramc ADD[5]	A0: siul_GPIO[163] A1: dramc_ADD[5] A2: ebi_ADD13 A3: flexpwm1_B[1]	I: _ I: _ I: _	—	disabled	DRAM ACC	VDD_HV_DRAM
AA4	GPIO	dspi1 CS3	A0: siul_GPIO[55] A1: dspi1_CS3 A2: lin2_TXD A3: dspi0_CS4	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
AA5	GPIO	flexpwm1 X[1]	A0: siul_GPIO[119] A1: flexpwm1_X[1] A2: etimer2_ETC[1] A3: dspi0_CS4	I: _ I: _ I: _	—	disabled	GP Slow/ Medium	VDD_HV_IO
AA6	ANA	adc3 AN[1]	—	siul_GPI[230]	AN: adc3_AN[1]	—	Analog	VDD_HV_ADR23
AA7	ANA	adc2_adc3 AN[12]	—	siul_GPI[226]	AN: adc2_adc3_AN[12]	—	Analog Shared	VDD_HV_ADR23
AA8	ANA	adc2 AN[0]	—	siul_GPI[221]	AN: adc2_AN[0]	—	Analog	VDD_HV_ADR23
AA11	ANA	adc0 AN[2]	—	siul_GPI[33]	AN: adc0_AN[2]	—	Analog	VDD_HV_ADR0
AA12	ANA	adc0 AN[5]	—	siul_GPI[66]	AN: adc0_AN[5]	—	Analog	VDD_HV_ADR0
AA13	ANA	adc0 AN[8]	—	siul_GPI[69]	AN: adc0_AN[8]	—	Analog	VDD_HV_ADR0

3.12 FMPLL electrical characteristics

Table 22. FMPLL electrical characteristics

No.	Symbol		Parameter	Conditions	Min	Typ	Max	Unit
1	$f_{REF\_CRYSTAL}$ f_{REF_EXT}	D	FMPLL reference frequency range[1, 2]	Crystal reference	4	—	120	MHz
2	f_{PLL_IN}	D	Phase detector input frequency range (after pre-divider)	—	4	—	16	MHz
3	$f_{FMPLLOUT}$	D	Clock frequency range in normal mode	See the FMPLL chapter in the chip reference manual for more details on PLL configuration.	16	—	256	MHz
4	f_{FREE}	P	Free running frequency	Measured using clock division (typically ÷16)	19	—	60	MHz
5	f_{sys}	D	On-chip FMPLL frequency[2]	—	—	—	180	MHz
6	t_{CYC}	D	System clock period	—	—	—	1 / f_{sys}	ns
7a	f_{LORL} f_{LORH}	D	Loss of reference frequency window[3]	Lower limit	1.6	—	3.7	MHz
7b				Upper limit	24	—	56	
8	f_{SCM}	D	Self-clocked mode frequency[4,5]	—	20	—	150	MHz
9	t_{LOCK}	P	Lock time	Stable oscillator (f_{PLLIN} = 4 MHz), stable V_{DD}	—	—	200	µs
10	t_{lpll}	D	FMPLL lock time [6, 7]	—	—	—	200	µs
11	t_{dc}	D	Duty cycle of reference	—	20	—	80	%
12a	C_{JITTER}	T	CLKOUT period jitter[8,9,10,11]	Peak-to-peak (clock edge to clock edge), $f_{FMPLLOUT}$ maximum[12]	—	—	160	ps
12b				Long-term jitter (avg. over 2 ms interval), $f_{FMPLLOUT}$ maximum	—	—	6	ns
13	Δt_{PKJIT}	T	Single period jitter (peak to peak)	PHI @ 16 MHz, Input clock @ 4 MHz	—	—	±500	ps
14	Δt_{LTJIT}	T	Long term jitter	PHI @ 16 MHz, Input clock @ 4 MHz	—	—	±6	ns
15	f_{LCK}	D	Frequency LOCK range	—	–4	—	+4	% $f_{FMPLLOUT}$
16	f_{UL}	D	Frequency un-LOCK range	—	–16	—	+16	% $f_{FMPLLOUT}$
17a	f_{CS} f_{DS}	D	Modulation Depth	Center spread	±0.25	—	±4	% $f_{FMPLLOUT}$
17b				Down Spread	–0.5	—	–8	
18	f_{MOD}	D	Modulation frequency[13]	31 < LDF[14] < 63 LDF > 63	—	—	(2240/LDF) 35	kHz

1 Considering operation with FMPLL not bypassed.

2 PFD clock range is 4– 16 MHz. An appropriate PLL Input division factor (IDF) should be chosen to divide the reference frequency to this range.

Equation 4 generates a constraint for external network design, in particular on resistive path. Internal switch resistances (R_{SW} and R_{AD}) can be neglected with respect to external resistances.

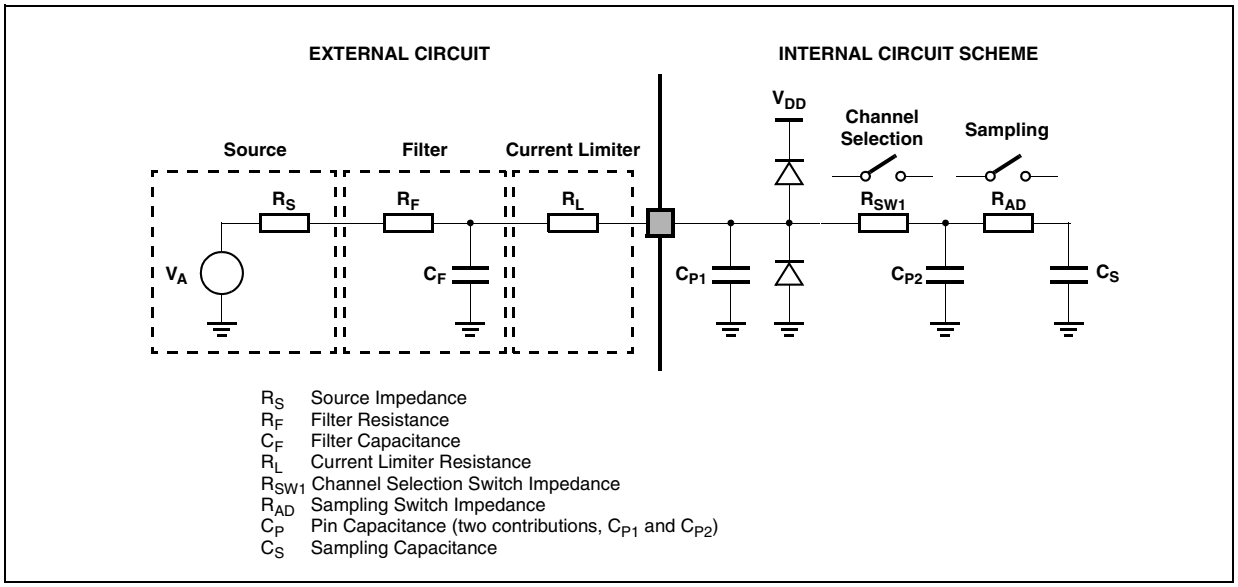


Figure 9. Input equivalent circuit

A second aspect involving the capacitance network shall be considered. Assuming the three capacitances C_F, C_{P1}, and C_{P2} are initially charged at the source voltage V_A (please see the equivalent circuit in Figure 9): A charge sharing phenomenon is installed when the sampling phase is started (A/D switch is closed).

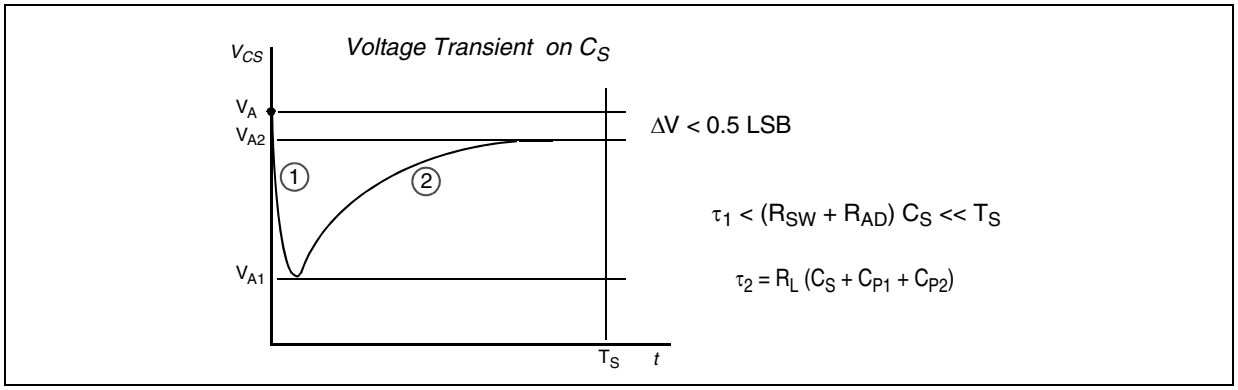


Figure 10. Transient behavior during sampling phase

In particular two different transient periods can be distinguished:

- A first and quick charge transfer from the internal capacitance C_{P1} and C_{P2} to the sampling capacitance C_S occurs (C_S is supposed initially completely discharged): considering a worst case (since the time constant in reality would be faster) in which C_{P2} is reported in parallel to C_{P1} (call $C_P = C_{P1} + C_{P2}$), the two capacitances C_P and C_S are in series, and the time constant is:

$$\tau_1 = (R_{SW} + R_{AD}) \bullet \frac{C_P \bullet C_S}{C_P + C_S} \qquad \textit{Eqn. 5}$$

Equation 5 can again be simplified considering only C_S as an additional worst condition. In reality, the transient is faster, but the A/D converter circuitry has been designed to be robust also in the very worst case: the sampling time T_S is always much longer than the internal time constant:

$$\tau_1 < (R_{SW} + R_{AD}) \bullet C_S \ll T_S \qquad \textit{Eqn. 6}$$

The charge of C_{P1} and C_{P2} is redistributed also on C_S, determining a new value of the voltage V_{A1} on the capacitance according to Equation 7:

$$V_{A1} \bullet (C_S + C_{P1} + C_{P2}) = V_A \bullet (C_{P1} + C_{P2}) \qquad \textit{Eqn. 7}$$

- A second charge transfer involves also C_F (that is typically bigger than the on-chip capacitance) through the resistance R_L: again considering the worst case in which C_{P2} and C_S were in parallel to C_{P1} (since the time constant in reality would be faster), the time constant is:

$$\tau_2 < R_L \bullet (C_S + C_{P1} + C_{P2}) \qquad \textit{Eqn. 8}$$

In this case, the time constant depends on the external circuit: in particular imposing that the transient is completed well before the end of sampling time T_S, a constraints on R_L sizing is obtained:

$$10 \bullet \tau_2 = 10 \bullet R_L \bullet (C_S + C_{P1} + C_{P2}) < T_S \qquad \textit{Eqn. 9}$$

Of course, R_L shall be sized also according to the current limitation constraints, in combination with R_S (source impedance) and R_F (filter resistance). Being C_F definitively bigger than C_{P1}, C_{P2} and C_S, then the final voltage V_{A2} (at the end of the charge transfer transient) will be much higher than V_{A1}. Equation 10 must be respected (charge balance assuming now C_S already charged at V_{A1}):

$$V_{A2} \bullet (C_S + C_{P1} + C_{P2} + C_F) = V_A \bullet C_F + V_{A1} \bullet (C_{P1} + C_{P2} + C_S) \qquad \textit{Eqn. 10}$$

The two transients above are not influenced by the voltage source that, due to the presence of the R_FC_F filter, is not able to provide the extra charge to compensate the voltage drop on C_S with respect to the ideal source V_A; the time constant R_FC_F of the filter is very high with respect to the sampling time (T_S). The filter is typically designed to act as anti-aliasing.

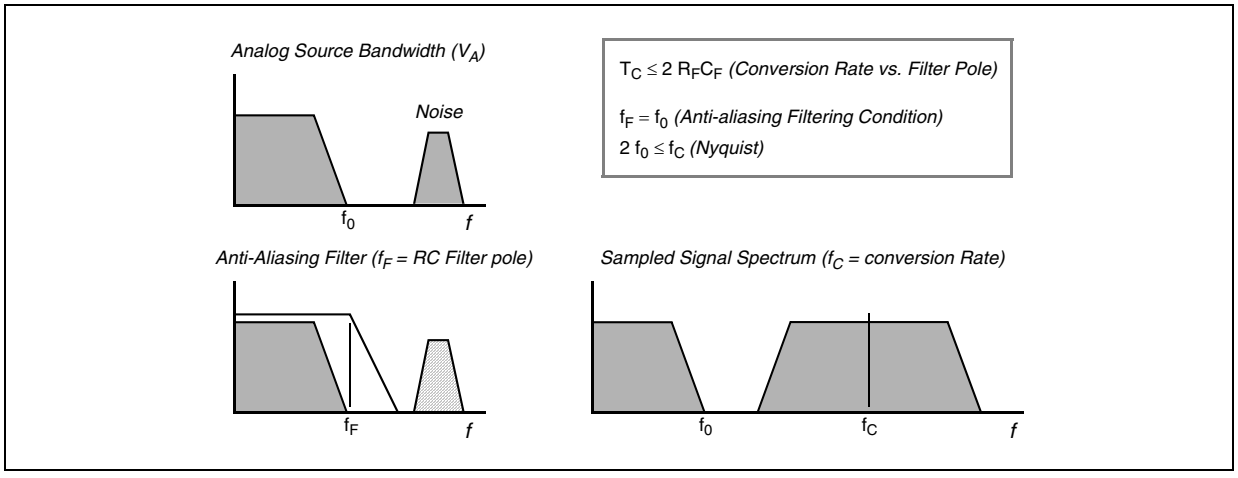


Figure 11. Spectral representation of input signal

Calling f_0 the bandwidth of the source signal (and as a consequence the cut-off frequency of the anti-aliasing filter, f_F), according to the Nyquist theorem the conversion rate f_C must be at least $2f_0$; it means that the constant time of the filter is greater

3.15.2 Read access timing

Table 28. Code flash read access timing

No.	Symbol		Parameter	Condition	Value	Unit
					Max	
1	f_{READ}	CC	Maximum frequency for Flash reading (system clock frequency SYS_CLK)	4 wait states	90	MHz
2				3 wait states	60	MHz

Table 29. Data flash read access timing

No.	Symbol		Parameter	Condition	Value	Unit
					Max	
1	f_{READ}	CC	Maximum frequency for Flash reading (system clock frequency SYS_CLK)	12 wait states	90	MHz
2				8 wait states	60	MHz

3.15.3 Write access timing

Table 30. Code flash write access timing

No.	Symbol		Parameter	Condition	Value	Unit
					Max	
1	f_{WRITE}	CC	Maximum frequency for Flash writing (system clock frequency SYS_CLK)	—	90	MHz

Table 31. Data flash write access timing

No.	Symbol		Parameter	Condition	Value	Unit
					Max	
1	f_{WRITE}	CC	Maximum frequency for Flash writing (system clock frequency SYS_CLK)	—	90	MHz

3.16 SRAM memory electrical characteristics

Table 32. System SRAM memory read/write access timing

No.	Symbol		Parameter	Condition	Value	Unit
					Max	
1	$s_{READ/WRITE}$	CC	Maximum frequency for system SRAM reading/writing (system clock frequency SYS_CLK)	1 wait state	90	MHz

supplied with 2.5 V. If a pad must be connected to a 3.3V device, its local VDD_HV_PDI must be 3.3 V. Injection current is then handled by the intrinsic diodes from the pad transistors and by the ESD diodes.

  - VDD_HV_PDI range 1.8 V to 3.3 V, as specified in the following tables
- Receiver
  - Selectable hysteresis input buffer
  - CMOS Input Buffer

The electrical data provided in this section applies:

- To the pads listed in Table 35
- Over the voltage range 1.62–3.6 V

Table 35. PDI I/O pads

No.	Name	Voltage	Used for	Notes
1	PDI Fast	1.62–3.6 V	I/O	Enhanced operating voltage range fast slew-rate output with four selectable slew-rates. Contains an input buffer and weak pullup/pulldown.
2	PDI Medium			Enhanced operating voltage range medium slew-rate output with four selectable slew-rates. Contains an input buffer and weak pullup/pulldown.

Table 36. PDI pads DC electrical characteristics[1]

No.	Symbol		Parameter	Min	Max	Unit
1	$V_{DD\_HV\_PDI}$	SR	I/O supply voltage	1.62	3.6	V
2	V_{IH_C}	CC	CMOS input buffer high voltage (hysteresis enabled)	$0.65 \times V_{DD\_HV\_PDI}$	$V_{DD\_HV\_PDI} + 0.3$	V
3	V_{IH_C}	CC	CMOS input buffer high voltage (hysteresis disabled)	$0.58 \times V_{DD\_HV\_PDI}$	$V_{DD\_HV\_PDI} + 0.3$	V
4	V_{IL_C}	CC	CMOS input buffer low voltage (hysteresis enabled)	$V_{SS} - 0.3$	$0.35 \times V_{DD\_HV\_PDI}$	V
5	V_{IL_C}	CC	CMOS input buffer low voltage (hysteresis disabled)	$V_{SS} - 0.3$	$0.42 \times V_{DD\_HV\_PDI}$	V
6	V_{HYS_C}	CC	CMOS input buffer hysteresis	$0.1 \times V_{DD\_HV\_PDI}$	—	V
7	I_{ACT_S}	CC	Selectable weak pullup/pulldown current	25	150	µA
8	V_{OH}	CC	Output high voltage	$0.8 \times V_{DD\_HV\_PDI}$	—	V
9	V_{OL}	CC	Output low voltage	—	$0.2 \times V_{DD\_HV\_PDI}$	V

1 Over- and undershoots occurring due to impedance mismatch of the external driver and the transmission line at PDI pads in input mode can be allowed up to 0.7 V repeatedly throughout the product expected lifetime and will not cause any long term reliability issue.

Table 37. Drive current

Pad	Drive Mode	Minimum I_{OH} (mA)[1]	Minimum I_{OL} (mA)[2]
PDI Fast	All	26.2	84.8
PDI Medium	All	19.2	52.1

1 I_{OH} is defined as the current sourced by the pad to drive the output to V_{OH}.

2 I_{OL} is defined as the current sunk by the pad to drive the output to V_{OL}.

Table 44. DRAM pads DC electrical specifications ($V_{DD\_HV\_DRAM}$ = 2.5 V) (continued)

No.	Symbol		Parameter	Condition	Min	Max	Unit
4	V_{IH}	CC	Input high voltage	—	$V_{DD\_HV\_DRAM\_VREF}$ + 0.15	—	V
5	V_{IL}	CC	Input low voltage	—	—	$V_{DD\_HV\_DRAM\_VREF}$ – 0.15	V
6	V_{OH}	CC	Output high voltage	—	$V_{DD\_HV\_DRAM\_VTT}$ + 0.81	—	V
7	V_{OL}	CC	Output low voltage	—	—	$V_{DD\_HV\_DRAM\_VTT}$ – 0.81	V

1 473 MAPBGA: Termination voltage can be supplied via package pins. 257 MAPBGA Termination voltage internally tied as the 257 MAPBGA does not provide DRAM interface. Disable ODT.

Table 45. Output drive current @ V_{DDE} = 2.5 V (±200 mV)

Pad Name	Drive Mode	Minimum I_{OH} (mA)[1]	Minimum I_{OL} (mA)[2]
DRAM ACC	011	–16.2	16.2
DRAM DQ	011		
DRAM CLK	011		

1 I_{OH} is defined as the current sourced by the pad to drive the output to V_{OH}.

2 I_{OL} is defined as the current sunk by the pad to drive the output to V_{OL}.

Table 46. DRAM pads AC electrical specifications ($V_{DD\_HV\_DRAM}$ = 2.5 V)

No.	Pad Name	Prop. Delay (ns) L → H/H → L[1]		Rise/Fall Edge (ns)		Drive Load (pF)	Drive/Slew Rate Select
		Min	Max	Min	Max		MSB, LSB
1	DRAM ACC	1.4/1.5	2.5/2.4	2.1/2.1	4.3/4.1	5	011
		1.7/1.7	2.8/2.7	0.6/0.7	1.1/1.3	20	
2	DRAM DQ	1.4/1.5	2.5/2.4	2.1/2.1	4.3/4.1	5	011
		1.7/1.7	2.8/2.7	0.6/0.7	1.1/1.3	20	
3	DRAM CLK	1.4/1.4	2.4/2.4	2.1/2.1	4.4/4.1	5	011
		1.6/1.6	2.7/2.7	0.6/0.7	1.6/1.8	20	

1 L → H signifies low-to-high propagation delay and H → L signifies high-to-low propagation delay.

3.19.3 DRAM pads electrical specification ($V_{DD\_HV\_DRAM}$ = 1.8 V)

Table 47. DRAM pads DC electrical specifications ($V_{DD\_HV\_DRAM}$ = 1.8 V)

No.	Symbol		Parameter	Condition	Min	Max	Unit
1	$V_{DD\_HV\_DRAM}$	SR	I/O supply voltage	—	1.62	1.9	V

JEDEC standards define the minimum set of requirements for compliant memory devices:

- JEDEC STANDARD, DDR2 SDRAM SPECIFICATION, JESD79-2C, MAY 2006
- JEDEC STANDARD, Double Data Rate (DDR) SDRAM Specification, JESD79E, May 2005
- JEDEC STANDARD, Low Power Double Data Rate (LPDDR) SDRAM Specification, JESD79-4, May 2006

The MPC5675K supports the configuration of two output drive strengths for DDR2 and LPDDR:

- Full drive strength
- Half drive strength (intended for lighter loads or point-to-point environments)

The MPC5675K memory controller supports dynamic on-die termination in the host device and in the DDR2 memory device.

This section includes AC specifications for all DDR SDRAM pins. The DC parameters are specified in the Section 3.19, DRAM pad specifications.

3.22.1.1 DDR and DDR2 SDRAM AC timing specifications

Table 55. DDR and DDR2 (DDR2-400) SDRAM timing specifications

At recommended operating conditions with $V_{DD\_MEM\_IO}$ of ±5%

No.	Symbol		Parameter	Min	Max	Unit
1	t_{CK}	CC	Clock cycle time, CL = *x*	—	90	MHz
2	$V_{IX\text{-}AC}$	CC	MCK AC differential crosspoint voltage[1]	$V_{DD\_MEM\_IO}$ × 0.5 – 0.1	$V_{DD\_MEM\_IO}$ × 0.5 + 0.1	V
3	t_{CH}	CC	CK HIGH pulse width[1, 2]	0.47	0.53	t_{CK}
4	t_{CL}	CC	CK LOW pulse width[1, 2]	0.47	0.53	t_{CK}
5	t_{DQSS}	CC	Skew between MCK and DQS transitions[2, 3]	–0.25	0.25	t_{CK}
6	$t_{OS(base)}$	CC	Address and control output setup time relative to MCK rising edge[2, 3]	(t_{CK}/2 – 750)		ps
7	$t_{OH(base)}$	CC	Address and control output hold time relative to MCK rising edge[2, 3]	(t_{CK}/2 – 750)	—	ps
8	$t_{DS1(base)}$	CC	DQ and DM output setup time relative to DQS[2, 3]	(t_{CK}/4 – 500)	—	ps
9	$t_{DH1(base)}$	CC	DQ and DM output hold time relative to DQS[2, 3]	(t_{CK}/4 – 500)	—	ps
10	t_{DQSQ}	CC	DQS-DQ skew for DQS and associated DQ inputs[2]	–(t_{CK}/4 – 600)	(t_{CK}/4 – 600)	ps

1 Measured with clock pin loaded with differential 100 Ω termination resistor.

2 All transitions measured at mid-supply ($V_{DD\_MEM\_IO}$/2).

3 Measured with all outputs except the clock loaded with 50 Ω termination resistor to $V_{DD\_MEM\_IO}$/2.

Figure 22 shows the DDR SDRAM write timing.

Table 64. DSPI timing (continued)

No.	Symbol		Parameter	Conditions	Min	Max	Unit
6	t_{DIS}	CC	Slave SOUT disable time	$\overline{SS}$ inactive to SOUT High-Z or invalid	—	10	ns
7	t_{PCSC}	CC	PCSx to $\overline{PCSS}$ time	—	13	—	ns
8	t_{PASC}	CC	$\overline{PCSS}$ to PCS*x* time	—	13	—	ns
9	t_{SUI}	CC	Data setup time for inputs	Master (MTFE = 0)	20	—	ns
				Slave	2	—	
				Master (MTFE = 1, CPHA = 0)	5	—	
				Master (MTFE = 1, CPHA = 1)	20	—	
10	t_{HI}	CC	Data hold time for inputs	Master (MTFE = 0)	–5	—	ns
				Slave	4	—	
				Master (MTFE = 1, CPHA = 0)	11	—	
				Master (MTFE = 1, CPHA = 1)	–5	—	
11	t_{SUO}	CC	Data valid (after SCK edge)	Master (MTFE = 0)	—	4	ns
				Slave	—	23	
				Master (MTFE = 1, CPHA = 0)	—	11	
				Master (MTFE = 1, CPHA = 1)	—	5	
12	t_{HO}	CC	Data hold time for outputs	Master (MTFE = 0)	–2	—	ns
				Slave	6	—	
				Master (MTFE = 1, CPHA = 0)	6	—	
				Master (MTFE = 1, CPHA = 1)	–2	—	
13	t_{DT}	CC	Delay after Transfer (minimum $\overline{CS}$ negation time)	Continuous mode Non-continuos mode[2]	62 134	— —	ns

1 Slave Receive Only Mode can operate at a maximum frequency of 60 MHz. Note that in this mode, the DSPI can receive data on SIN, but no valid data is transmitted on SOUT.

2 In non-continuous mode, this value is always t_{SCK} × DSPI_CTAR*n*[DT] × DSPI_CTAR*n*[PDT]. The minimum permissible value of DT is 2 and the minimum permissible value of PDT is 1. See the DSPI chapter of the *MPC5675K Reference Manual* for more information.

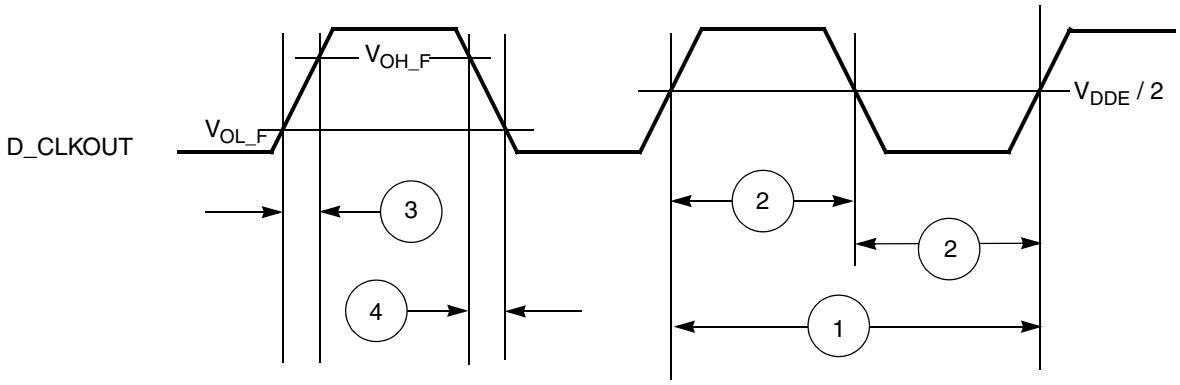


Figure 49. D_CLKOUT timing

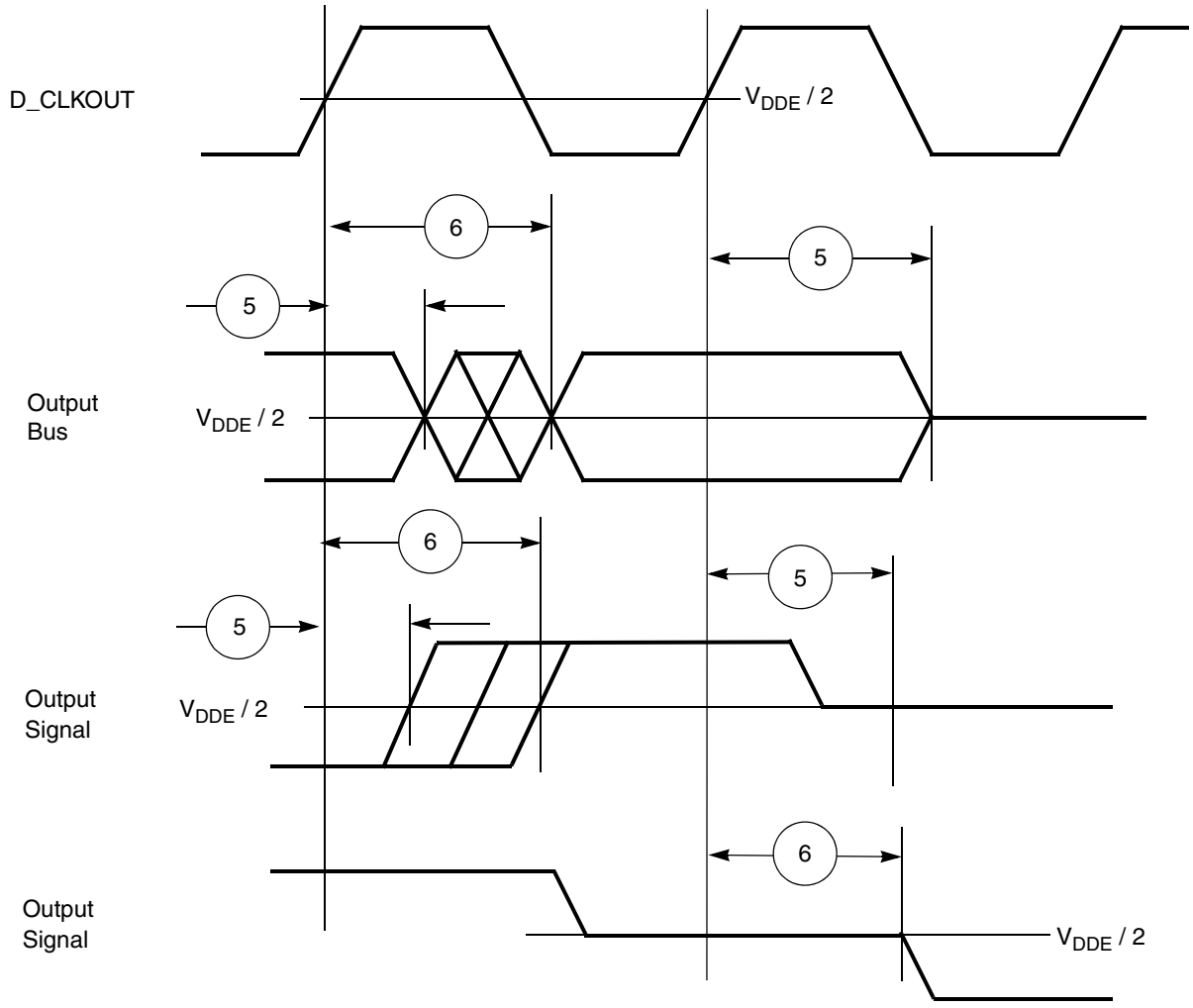


Figure 50. Synchronous output timing

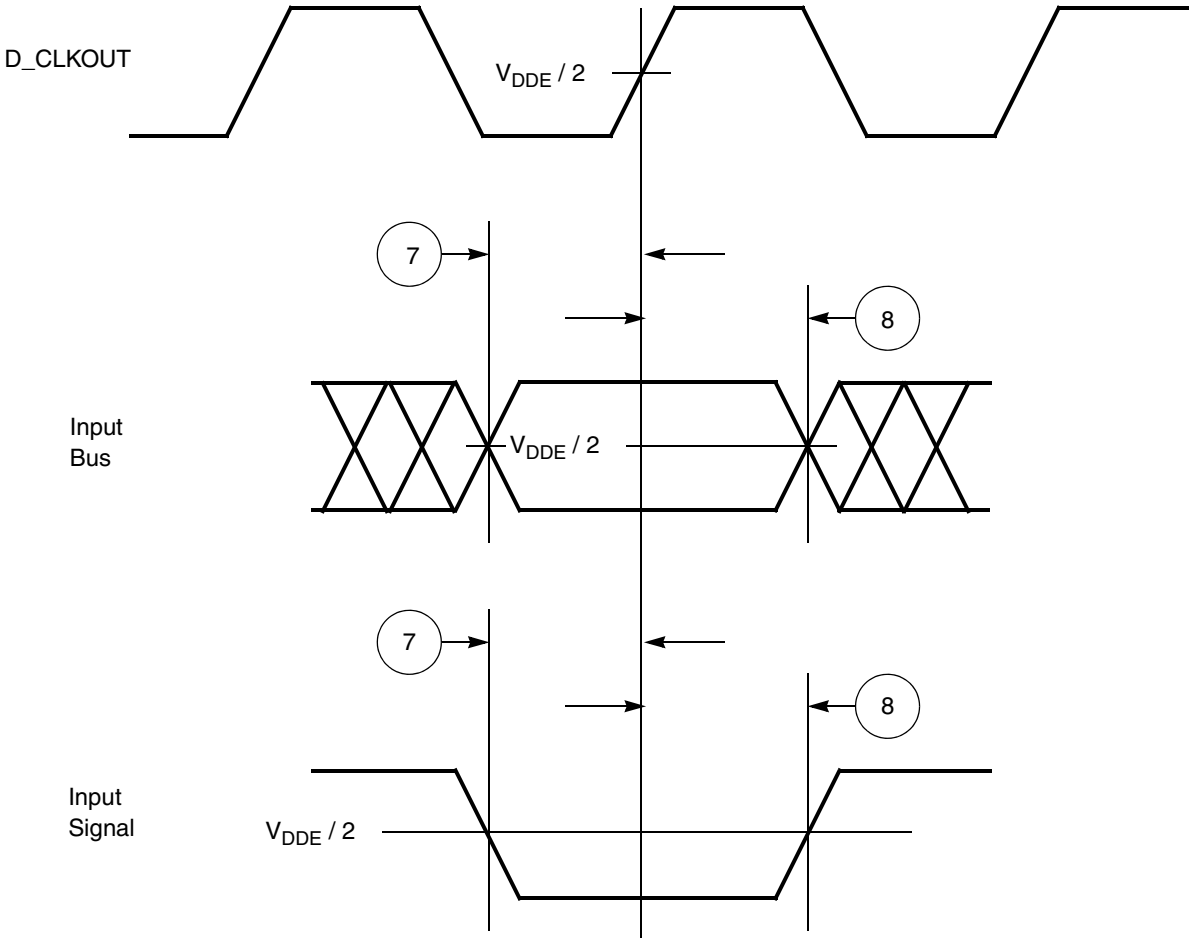


Figure 51. Synchronous input timing

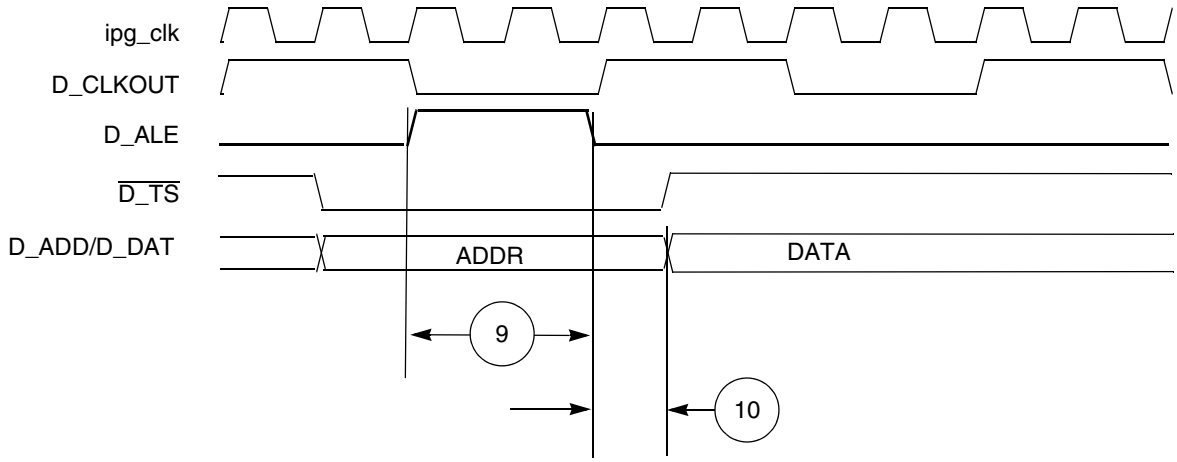


Figure 52. ALE signal timing

REVISION HISTORY

DOCUMENT NO: 98ASA00096D
PAGE: 2089
REV: O

LTR	ORIGINATOR	REVISIONS	DRAFTER	DATE
O	D. VO	RELEASED FOR PRODUCTION	DSS	08 JUN 2009

TITLE:	CASE NUMBER: 2089–01	
473 I/O, FINE PITCH, PBGA, 19 X 19 PKG, 0.8MM PITCH (MAP)	STANDARD: NON–JEDEC	
	PACKAGE CODE:IN AGILE	SHEET: 3

Figure 58. 473 MAPBGA package mechanical data (3 of 3)

Table 73. Revision history (continued)

Revision	Date	Description of Changes
6 (cont.)	6 Feb 2012	In Table 62 (External interrupt timing (GPIO IRQ)): • Changed T_{IPWL} min value from TBD to 3. • Changed T_{IPWH} min value from TBD to 3. • Changed T_{ICYC} min value from TBD to 6. • Changed all units from ns to t_{CYC}. In Table 71 (I^2C SCL and SDA input timing specifications), corrected the line numbering.
6.1	30 Mar 2012	No content changes, technical or editorial, were made in this revision. Change bars are identical to those in Rev. 6. Removed the “preliminary” footers throughout. Changed “Data Sheet: Advance Information” to “Data Sheet: Technical Data” on page 1. Removed the “product under development” disclaimer on page 1.
7	18 May 2012	Minor editorial changes and improvements throughout. In Section 1.3, Device comparison, Table 1 (MPC5675K family device comparison), changed the CPU/Data Cache entry from "16 KB, 4-way with EDC (SoR)" to "16 KB, 4-way with Parity (SoR)". In Section 1.3, Device comparison, Table 1 (MPC5675K family device comparison), added footnotes to stipulate the peripheral instances that are used on derivative devices: • Added footnote to **MPC5673K** DSPI module: “DSPI_0 and DSPI_1.“ • Added footnote to **MPC5673K** I2C module: “I2C_0 and I2C_1.“ • Added footnote to **MPC5673K** LinFlex module: “LinFlex_0, LinFlex_1, and LinFlex_2“ In Section 1.4, Block diagram: • Added missing modules (PMC, SPE2, VLE, and flash. • Added an arrow each from Core_0 and Core_1 to the XBAR modules to represent the data path. • Updated the Redundancy Checkers to reflect the actual implementation. • Renamed the “JTAG/Nexus” block to “Debug”, with JTAG and Nexus shown as submodules. In Section 1.5, Feature list, changed “Junction temperature sensor” to “Silicon substrate (die) temperature sensor”. In Section 1.6.1, High-performance e200z7d core processor and Section 1.6.9, Cache memory, removed the bullet “Supports tag and data parity" and added the following bullets: — Supports tag and data cache parity — Supports EDC for instruction cache In Section 1.6.19, System Timer Module (STM), changed “Duplicated periphery to guarantee that safety targets (SIL3) are achieved” to “Replicated periphery to provide safety measures respective to high safety integrity levels (for example, SIL 3, ASIL D)” In Section 1.6.20.2, Cross Triggering Unit (CTU), changed “DMA support with safety features” to “Supports safety measures using DMA”. In Section 1.6.21, Redundancy Control and Checker Unit (RCCU), changed “Duplicated module to guarantee highest possible diagnostic coverage (check of checker)” to “Duplicated module to enable high diagnostic coverage (check of checker)”. In Section 1.6.22, Software Watchdog Timer (SWT), • Changed “Duplicated periphery to guarantee that safety targets (SIL3) are achieved” to “Replicated periphery to provide safety measures respective to high safety integrity levels (for example, SIL 3, ASIL D)”. • Changed “Allows high level of safety (SIL3 monitor)” to “Provides measures to target high safety integrity levels (for example, SIL 3, ASIL D)”. In Section 1.6.25, Cyclic Redundancy Checker (CRC) unit, in the sentence “Key engine to be coupled with communication periphery where CRC application is added to allow implementation of safe communication protocol”, changed “allow” to “support”.